



2N7000 2N7002

N-channel 60 V, 1.8 Ω , 0.35 A, SOT23-3L, TO-92
STripFET™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
2N7000	60 V	< 5 Ω (@10V)	0.35 A
2N7002	60 V	< 5 Ω (@10V)	0.20 A

- Low Q_g
- Low threshold drive

Application

- Switching applications

Description

This Power MOSFET is the second generation of STMicroelectronics unique “single feature size” strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

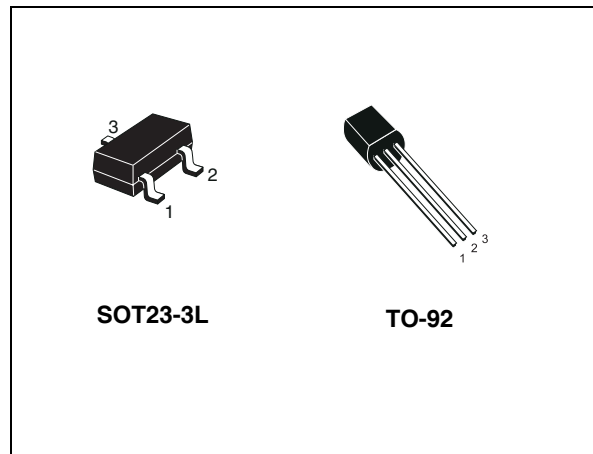


Figure 1. Internal schematic diagram

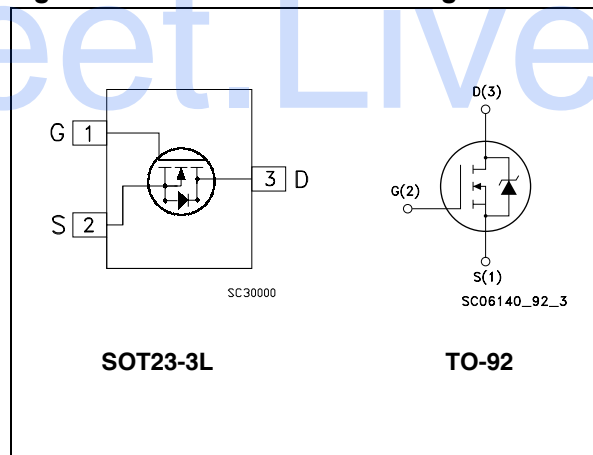


Table 1. Device summary

Order codes	Marking	Package	Packaging
2N7000	2N7000G	TO-92	Bulk
2N7002	ST2N	SOT23-3L	Tape and reel

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-92	SOT23-3L	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	60		V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	60		V
V_{GS}	Gate- source voltage	± 18		V
I_D	Drain current (continuous) at $T_C = 25 \text{ }^\circ\text{C}$	0.35	0.20	A
$I_{DM}^{(1)}$	Drain current (pulsed)	1.4	1	A
P_{TOT}	Total dissipation at $T_C = 25 \text{ }^\circ\text{C}$	1	0.35	W

1. Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-92	SOT23-3L	
$R_{thj-amb}$	Thermal resistance junction-ambient max	125	357.1 ⁽¹⁾	$^\circ\text{C}/\text{W}$
T_J	Operating junction temperature	- 55 to 150		$^\circ\text{C}$
T_{stg}	Storage temperature			

1. When mounted on 1inch² FR-4, 2 Oz copper board.

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	60			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}$, $T_C = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 18\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1	2.1	3	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 0.5\text{ A}$		1.8 2	5 5.3	Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 10\text{ V}$, $I_D = 0.5\text{ A}$		0.6		S
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		43		pF
C_{oss}	Output capacitance			20		pF
C_{rss}	Reverse transfer capacitance			6		pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\text{ V}$, $I_D = 0.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (see Figure 16)		5		ns
t_r	Rise time			15		ns
$t_{d(off)}$	Turn-off delay time			7		ns
t_f	Fall time			8		ns
Q_g	Total gate charge	$V_{DD} = 30\text{ V}$, $I_D = 1\text{ A}$, $V_{GS} = 5\text{ V}$ (see Figure 17)		1.4	2	nC
Q_{gs}	Gate-source charge			0.8		nC
Q_{gd}	Gate-drain charge			0.5		nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				0.35 1.40	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 1\text{ A}$, $V_{GS} = 0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 1\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 20\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 18)		32 25 1.6		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark.

Table 8. SOT23-3L mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			1.25
A1	0		0.15
A2	1.00		1.20
A3	0.60		0.70
D	2.826		3.026
E	2.60		3.00
E1	1.526		1.726
e		0.95	
e1		1.90	
L	0.35		0.60
L1		0.59	
L2		0.25	
R	0.05		
R1	0.05		0.20
K	3°		7°
K1	6°		10°

Figure 23. SOT23-3L drawing

